



2N50-CBS

Preliminary

Power MOSFET

**2.0A, 500V N-CHANNEL
POWER MOSFET**

■ DESCRIPTION

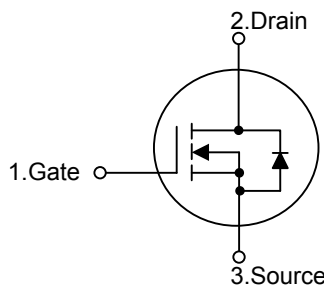
The UTC **2N50-CBS** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **2N50-CBS** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

■ FEATURES

- * $R_{DS(ON)} < 5.6\Omega @ V_{GS}=10V, I_D=1.0A$
- * High Switching Speed
- * 100% Avalanche Tested

■ SYMBOL

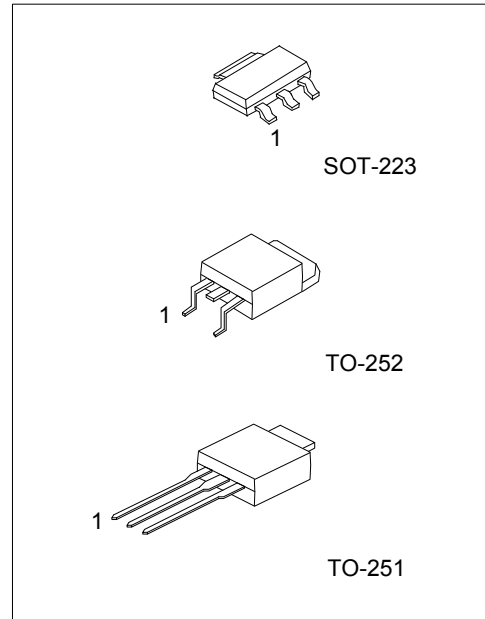


■ ORDERING INFORMATION

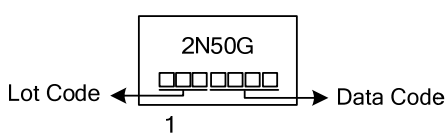
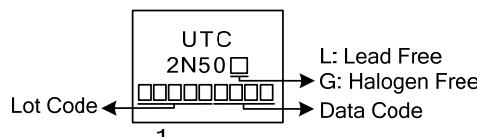
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	2N50G-AA3-R	SOT-223	G	D	S	Tape Reel
2N50L-TM3-T	2N50G-TM3-T	TO-251	G	D	S	Tube
2N50L-TN3-R	2N50G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>2N50G-AA3-R</p>	<p>(1) R: Tape Reel, T: Tube (2) AA3: SOT-223, TM3: TO-251, TN3: TO-252 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING

SOT-223	TO-251 / TO-252
 <p>2N50G Lot Code ← 1 → Data Code</p>	 <p>UTC 2N50 Lot Code ← 1 → Data Code L: Lead Free G: Halogen Free</p>

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■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	2 (Note 3)	A
	Pulsed (Note 2)	I_{DM}	8 (Note 3)	A
Avalanche Current (Note 2)		I_{AR}	1.9	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	45	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.1	V/ns
Power Dissipation	SOT-223	P_D	8.9	W
	TO-251/TO-252		50	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=25\text{mH}$, $I_{AS}=1.9\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$.

4. $I_{SD}\leq 2.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	150	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		110	$^\circ\text{C}/\text{W}$
Junction to Case	SOT-223	θ_{JC}	14	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		2.5	$^\circ\text{C}/\text{W}$

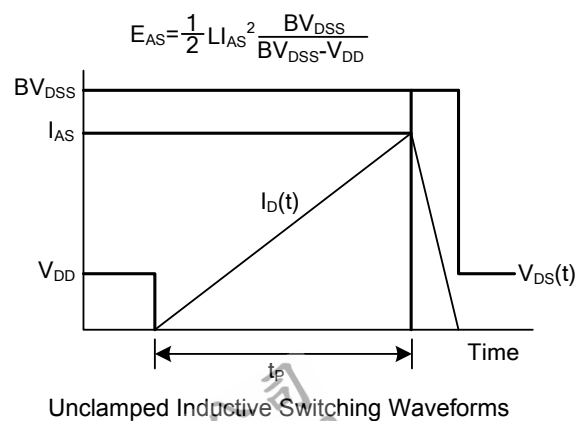
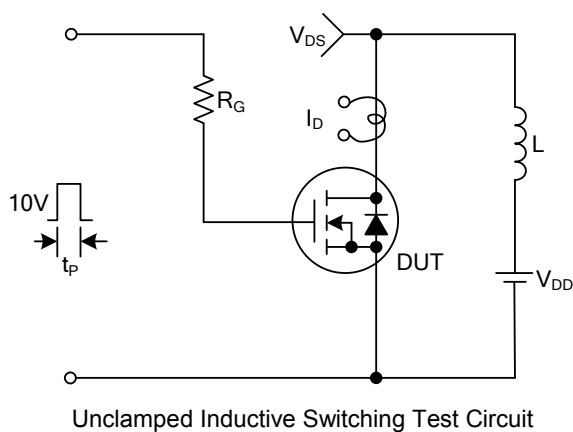
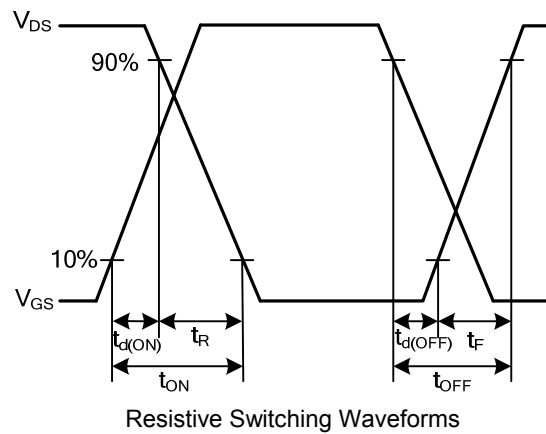
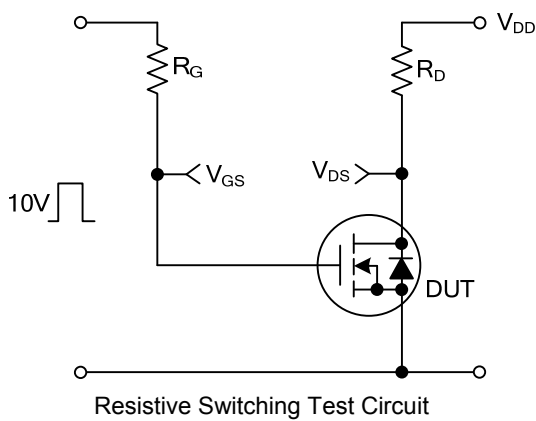
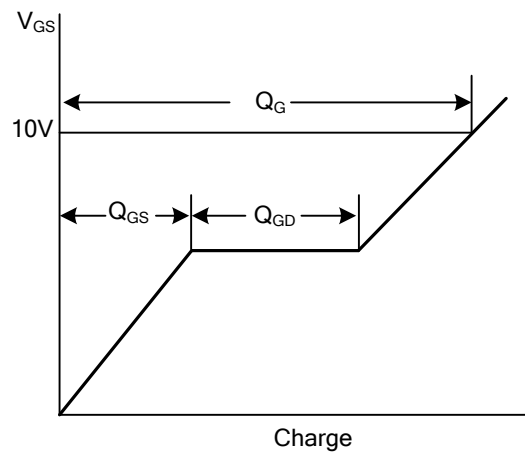
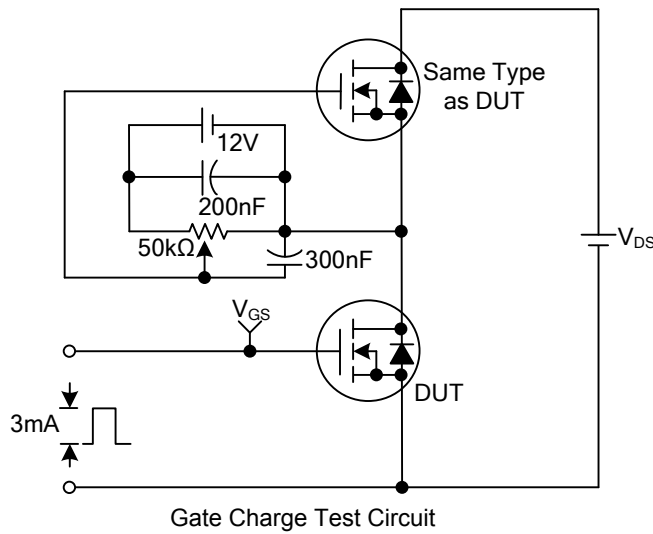
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	500			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$			25	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
	Reverse				-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=1.0\text{A}$			5.6	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		165		pF
Output Capacitance	C_{OSS}			20		pF
Reverse Transfer Capacitance	C_{RSS}			5		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=50\text{V}$, $V_{GS}=10\text{V}$, $I_D=1.3\text{A}$, $I_G=250\mu\text{A}$ (Note 1, 2)		17		nC
Gate to Source Charge	Q_{GS}			1.7		nC
Gate to Drain Charge	Q_{GD}			1.4		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{DD}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1, 2)		30		ns
Rise Time	t_R			17		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			105		ns
Fall-Time	t_F			28		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				2	A
Maximum Body-Diode Pulsed Current	I_{SM}				8	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=2\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$I_S=2\text{A}$, $V_{GS}=0\text{V}$, $dI_F/dt =$ $100\text{A}/\mu\text{s}$		190		ns
Reverse Recovery Charge	Q_{rr}			0.45		μC

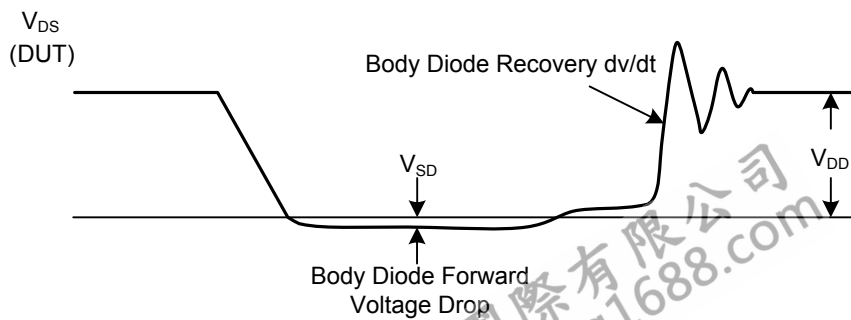
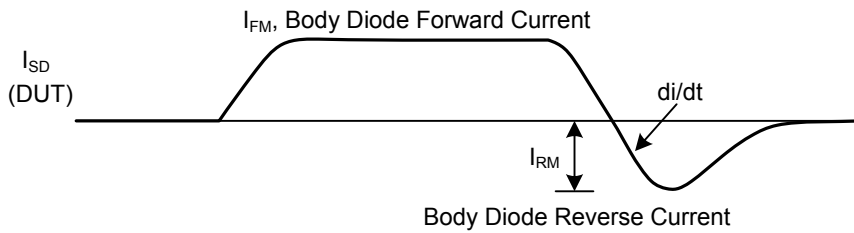
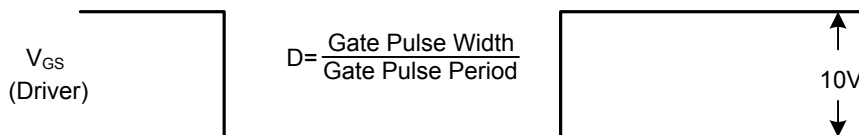
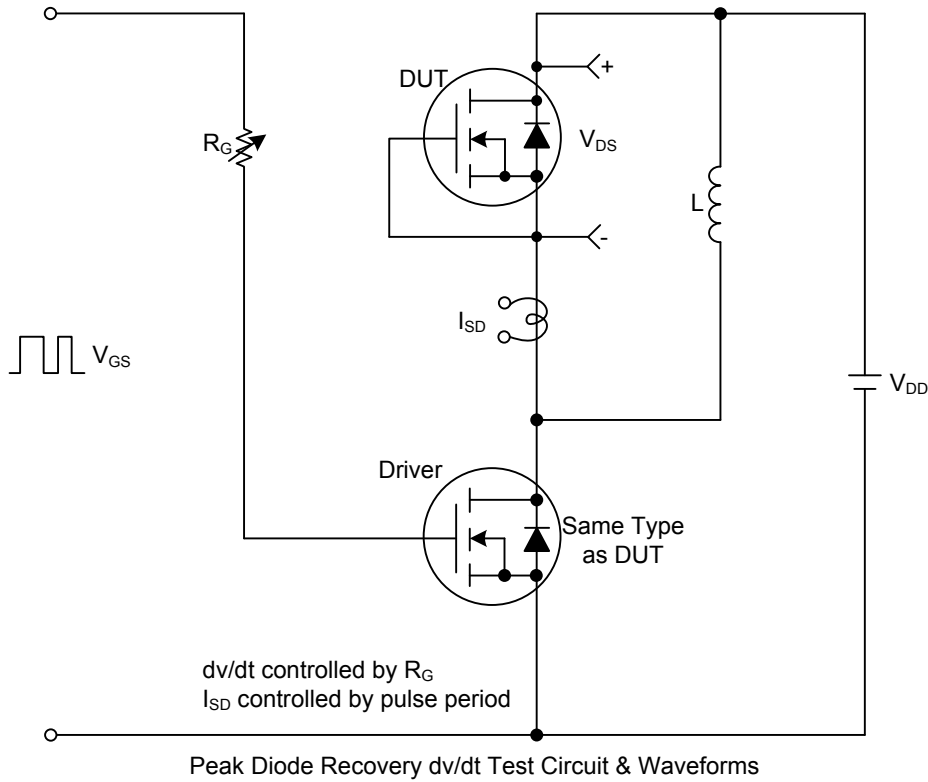
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



■ TEST CIRCUITS AND WAVEFORMS(Cont.)



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